Ordering number : ENA0263

SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET

2SK3979 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		200	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_D		6	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	24	A
Allowable Power Dissipation	P_D		1	W
		Tc=25°C	20	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	200			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=200V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±24V, V_{DS}=0V			±1	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	2.0		3.2	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=3A	2.1	3.5		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)$	I_D=3A, V_{GS}=10V		320	450	mΩ
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		1090		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		85		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		35		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		17.5		ns
Rise Time	t_r	See specified Test Circuit.		26		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		50		ns
Fall Time	t_f	See specified Test Circuit.		42		ns

Marking : K3979

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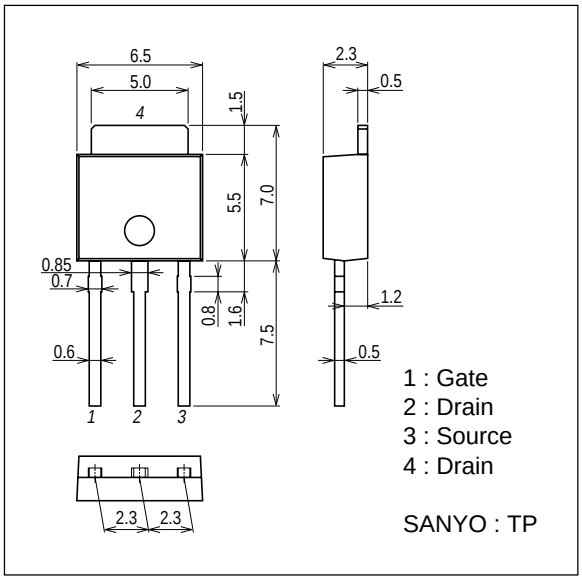
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V_{DS}=100V, V_{GS}=10V, I_D=6A		18.2		nC
Gate-to-Source Charge	Qgs	V_{DS}=100V, V_{GS}=10V, I_D=6A		8.0		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=100V, V_{GS}=10V, I_D=6A		7.0		nC
Diode Forward Voltage	V_{SD}	I_S=6A, V_{GS}=0V		0.86	1.2	V

Package Dimensions

unit : mm

7518-004



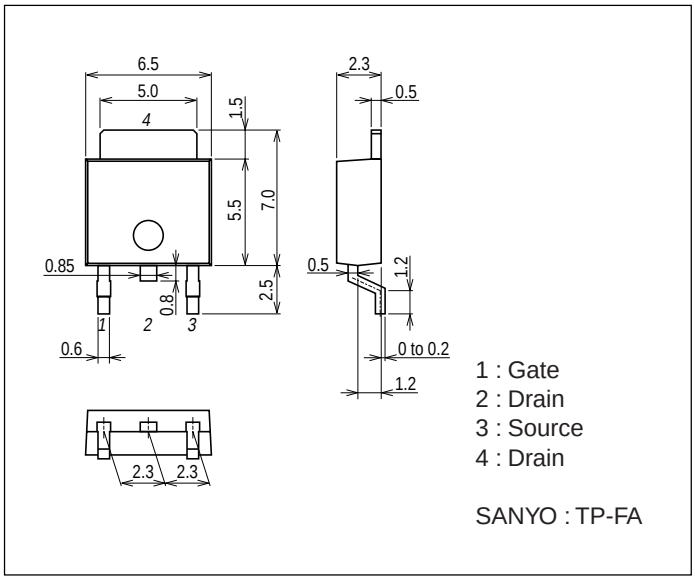
1 : Gate
2 : Drain
3 : Source
4 : Drain

SANYO : TP

Package Dimensions

unit : mm

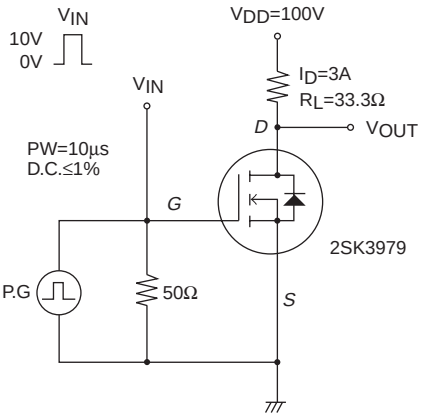
7003-004

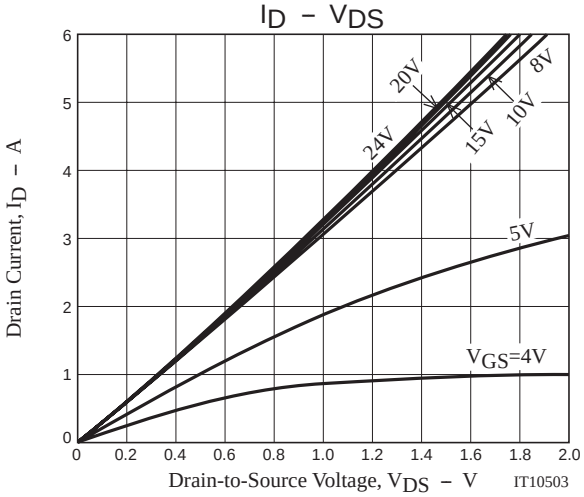


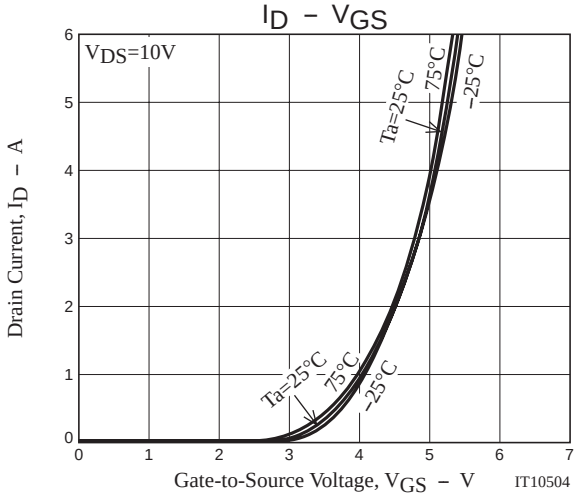
1 : Gate
2 : Drain
3 : Source
4 : Drain

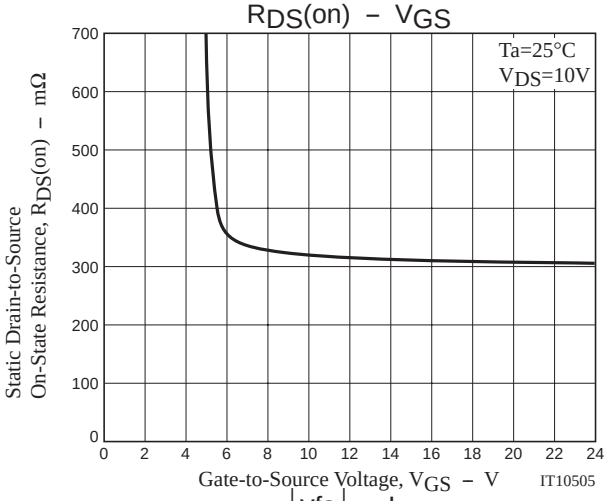
SANYO : TP-FA

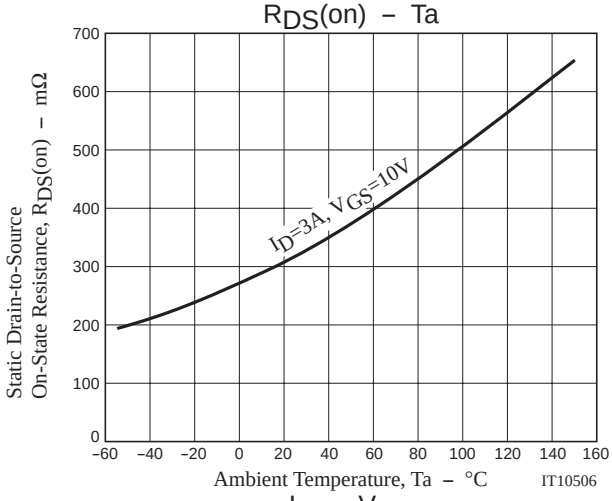
Switching Time Test Circuit

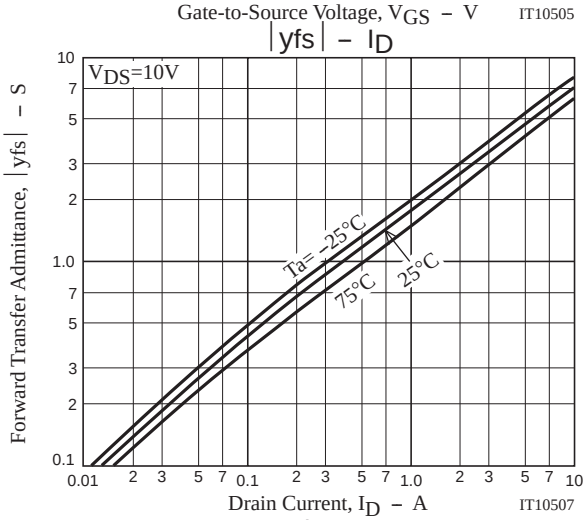


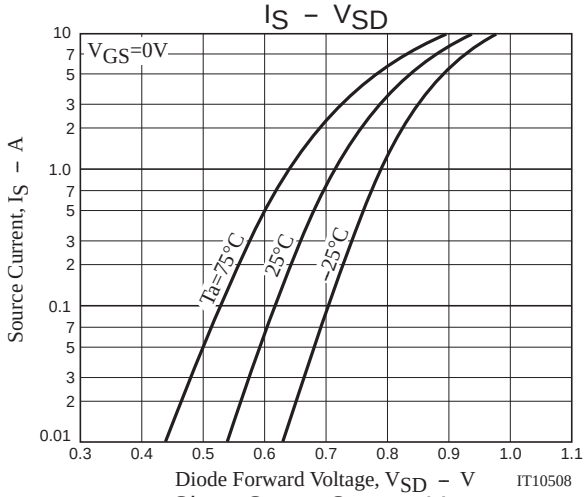


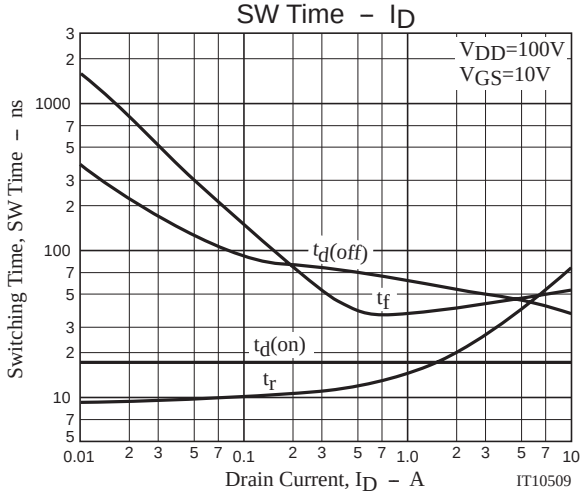


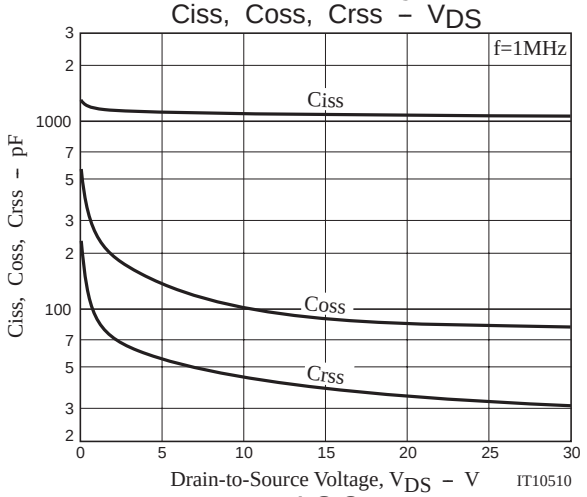

RDS(on) – VGS
Ta=25°C
VDS=10V
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT10505

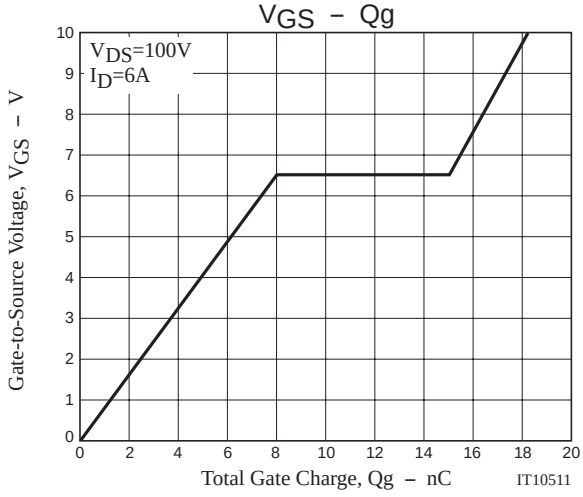

RDS(on) – Ta
ID=3A, VGS=10V
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT10506

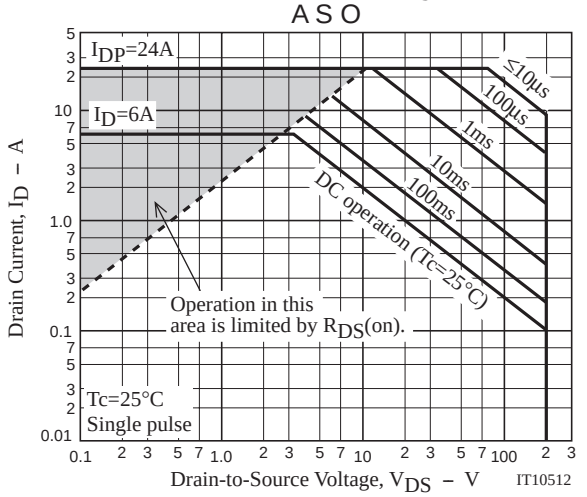

|yfs| – ID
VDS=10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT10507

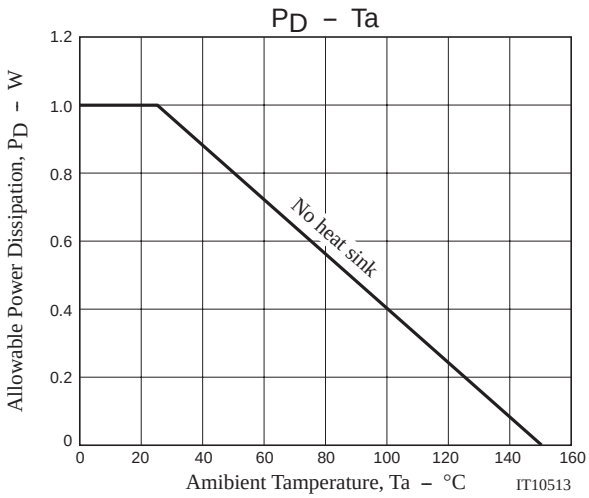

IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT10508

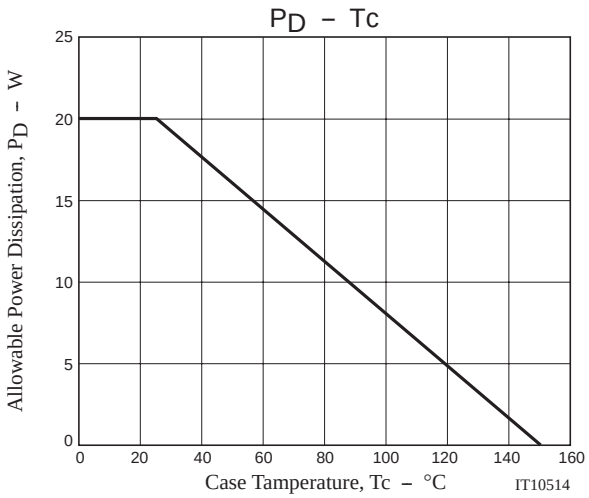

SW Time – ID
VDD=100V
VGS=10V
td(off)
tf
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT10509


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT10510


VGS – Qg
VDS=100V
ID=6A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT10511


A S O
IDP=24A
ID=6A
≤10μs
100μs
1ms
10ms
100ms
DC operation (Tc=25°C)
Operation in this area is limited by RDS(on).
Tc=25°C
Single pulse
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT10512





Note on usage : Since the 2SK3979 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.